

# Photoluminescence and Scintillation Properties of Ce-doped BaHfO<sub>3</sub> Crystals

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The photoluminescence (PL) and scintillation properties of Ce-doped BaHfO<sub>3</sub> crystals were investigated. The Ce-doped BaHfO<sub>3</sub> crystal is transparent and colorless after annealing treatment under a reduction condition. The broad luminescence band at ~370 nm was observed under ~280 nm excitation with the decay time of ~17 ns. The X-ray-induced scintillation spectra also showed the broad luminescence band at ~380 nm with a fast decay. The origin of the broad luminescence band at ~380 nm is attributed to the 5d–4f transition of Ce<sup>3+</sup>. The pulse height distribution under <sup>137</sup>Cs gamma ray irradiation using Ce-doped BaHfO<sub>3</sub> exhibited a distinguishable photoabsorption peak. The light yield of Ce-doped BaHfO<sub>3</sub> is ~1600 photons/MeV.

## 1. Introduction

Ionizing radiation detection is conducted by two measurement methods. One is a direct measurement using, for example, a Ge semiconductor detector. The other is an indirect measurement using, for example, a scintillation detector. A scintillation detector uses a scintillator, which generates luminescence under ionizing radiation irradiation. The generated luminescence is detected by a photodetector such as a photomultiplier tube (PMT) and a photodiode. For example, X-ray images are taken using a scintillation detector,<sup>(1)</sup> and positron emission tomography also uses many scintillators.<sup>(2)</sup> The typically required properties for scintillators are a high light yield and a fast decay time. Moreover, there are some requirements for density and effective atomic number for some applications. In particular, a high density and effective atomic number of materials are important for the detection of X- and gamma rays.<sup>(3)</sup> Scintillators with a fast decay are realized by luminescence from the 5d–4f transition of Ce<sup>3+</sup> or Pr<sup>3+</sup>.<sup>(4)</sup> Thus, scintillation properties have been investigated in Ce- or Pr-doped dense materials to develop a novel X- or gamma-ray scintillator.<sup>(5–12)</sup> Moreover, the scintillation properties of

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many materials such as single crystals,<sup>(13–22)</sup> ceramics,<sup>(23–27)</sup> and glasses<sup>(28–37)</sup> have been investigated.

$M\text{HfO}_3$  ( $M = \text{Ca, Sr, or Ba}$ ) have high density and effective atomic number. The scintillation properties of many Ce-doped  $M\text{HfO}_3$  have been investigated.<sup>(38–42)</sup> The light yield of a Ce-doped  $\text{CaHfO}_3$  single crystal, which has a density of  $6.9 \text{ g/cm}^3$ , is  $\sim 7800$  photons/MeV with a fast decay of  $\sim 22 \text{ ns}$ .<sup>(43)</sup> The light yield of Ce-doped  $\text{CaHfO}_3$  is increased by Mg substitution.<sup>(44)</sup> The density of a  $\text{SrHfO}_3$  single crystal is  $7.6 \text{ g/cm}^3$ , and the light yield is  $\sim 400$  photons/MeV.<sup>(45)</sup>  $\text{BaHfO}_3$  has the highest density of  $8.3 \text{ g/cm}^3$  among the  $M\text{HfO}_3$  series. The scintillation properties of Ce-doped  $\text{BaHfO}_3$  transparent ceramics have been investigated.<sup>(46)</sup> In this work, the integrated light yield was investigated; however, there is no report on the light yield of Ce-doped  $\text{BaHfO}_3$  determined from the pulse height distribution.

In this study, Ce-doped  $\text{BaHfO}_3$  crystals were synthesized by the floating zone (FZ) method, and the photoluminescence (PL) and X-ray-induced scintillation spectra and decay curves were measured. Finally, the pulse height distribution under  $^{137}\text{Cs}$  gamma-ray irradiation was investigated to estimate the quantitative light yield of Ce-doped  $\text{BaHfO}_3$ .

## 2. Materials and Methods

Ce-doped  $\text{BaHfO}_3$  crystals were synthesized by the FZ method. Four xenon lamps as a heating source were installed in the FZ instrument. The details of the equipment are found in Ref. 47. The feed rods were synthesized by a simple sintering method. The starting materials, namely,  $\text{BaCO}_3$  (99.99%, Rera Metallic),  $\text{HfO}_2$  (99.95%, Furuuchi Chemical), and  $\text{CeO}_2$  (99.99%, Furuuchi Chemical), were mixed using a mortar and pestle. The mixed powder was sintered at  $1200 \text{ }^\circ\text{C}$  for 8 h. The sintered powder was remixed and further sintered at  $1400 \text{ }^\circ\text{C}$  for 8 h. The resintered powder was hydrostatically pressed into a cylindrical rod and again sintered at  $1500 \text{ }^\circ\text{C}$  for 8 h. The amount of  $\text{BaCO}_3$  in this powder was increased by 30% from the stoichiometric composition of  $\text{BaHfO}_3$  to compensate for the volatilization of Ba during the crystal growth. The pulling-down rate was  $50 \text{ mm/h}$ , and the rotation rates of the upper and lower shafts were 28 and 25 rpm, respectively. The synthesized crystals were treated under a reduction atmosphere to suppress the formation of  $\text{Ce}^{4+}$  ions. The crystals were put into graphite powder under vacuum. The heating temperature was  $800 \text{ }^\circ\text{C}$ , and the treatment time was 96–144 h. The treatment time was determined on the basis of the appearance of the samples.

The measurement range of the X-ray diffraction (XRD) patterns was  $2\theta = 10$  to  $70$  degrees (Rigaku, Miniflex600), and the X-ray source was  $\text{CuK}\alpha$ . The PL excitation and emission map and quantum yield ( $QY$ ) were measured using the Hamamatsu Photonics C11347 spectrometer. The PL decay curves were also measured using the Hamamatsu Photonics C11367 spectrometer. The X-ray-induced scintillation spectra, decay curves, and afterglow curves were measured with original setups.<sup>(48,49)</sup> The voltage and current applied to the X-ray tube for the scintillation spectra were  $40 \text{ kV}$  and  $1.2 \text{ mA}$ , respectively. The pulse height distribution under  $^{137}\text{Cs}$  gamma-ray irradiation was measured using a laboratory-made setup.<sup>(48)</sup> The PMT used was of the ultra-bi-alkali type (Hamamatsu Photonics, R7600-200).

### 3. Results and Discussion

A photograph of the synthesized samples is shown in Fig. 1. The as-synthesized samples were brown. The 1 and 5% samples were transparent, and the 0.3 and 3% samples were opaque. The 0.3 and 1% samples were black because some graphite powders were inside the sample. The 3% sample was also partially black for the same reason. The 5% sample was orange. The as-synthesized sample was brown; thus, the treatment time or temperature of the 5% sample was insufficient compared with those of the other samples. To investigate the absorption wavelength, diffuse transmission spectra were measured, and the results are shown in Fig. 2. Absorption bands were observed at  $\sim 250$  and  $300$  nm in all the samples. In contrast, the 5% sample showed a deep absorption band at  $\sim 450$ – $550$  nm compared with the 1% sample. The 5% sample was orange, as shown in Fig. 1, because the absorption band was at  $\sim 450$ – $550$  nm. The transmittance of the 0.3% sample was the lowest among the samples, and the black color contributes to the low transmittance.

Figure 3 shows the XRD patterns of the synthesized samples and references. All the samples included  $\text{BaHfO}_3$  (ICDD. 24-0102) and monoclinic  $\text{HfO}_2$  (COD. 9013470). The melting point of  $\text{BaHfO}_3$  is quite high, and the vapor pressure of Ba is also high; thus, Ba was volatilized during crystal synthesis, and  $\text{HfO}_2$  remained in the samples. The XRD peak position did not seem to shift. The ionic radii of  $\text{Ba}^{2+}$  ( $1.61$  Å in twelve-coordination),  $\text{Hf}^{4+}$  ( $0.71$  Å in six-coordination),  $\text{Ce}^{3+}$  ( $1.34$  Å in twelve-coordination and  $1.01$  Å in six-coordination), and  $\text{Ce}^{4+}$  ( $1.14$  Å in twelve-coordination and  $0.87$  Å in six-coordination) are not the same in the same coordination number.<sup>(50)</sup> The doped Ce ions were considered to be incorporated into the Ba or Hf sites; thus, the peak shift was quite small.

Figure 4 shows the PL excitation and emission map of the 1% sample as the representative sample because the other samples also exhibit similar spectra but with a different intensity, and

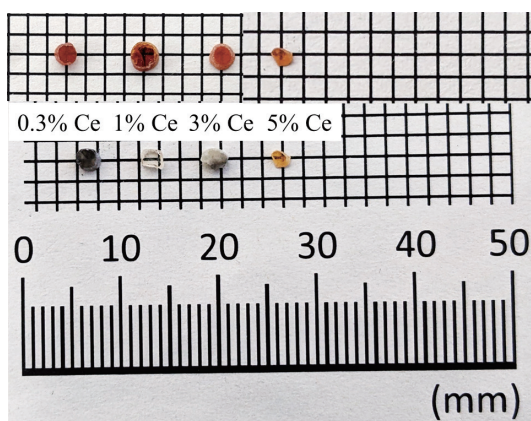


Fig. 1. (Color online) Photograph of as-synthesized (top) and treated Ce-doped  $\text{BaHfO}_3$  samples (bottom).

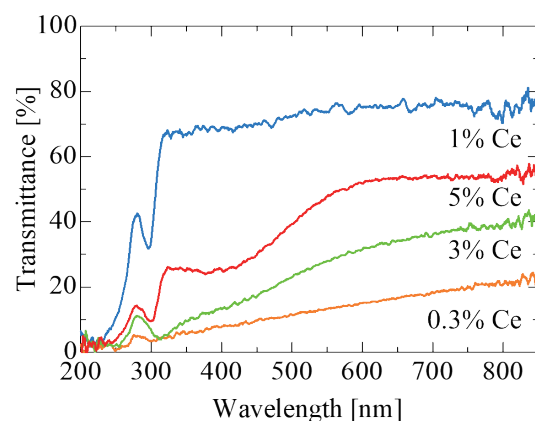


Fig. 2. (Color online) Diffuse transmission spectra of Ce-doped  $\text{BaHfO}_3$  samples.

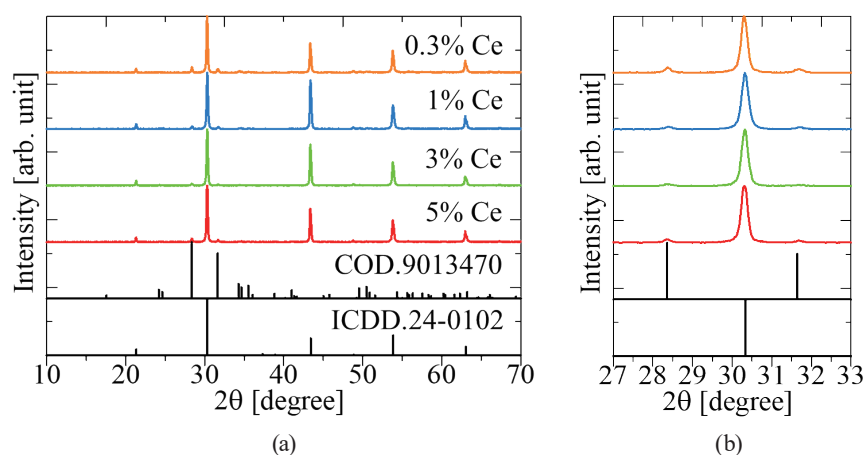


Fig. 3. (Color online) (a) XRD patterns of Ce-doped BaHfO<sub>3</sub> samples and references and (b) enlarged XRD patterns from  $2\theta = 27$  to 33 degrees.

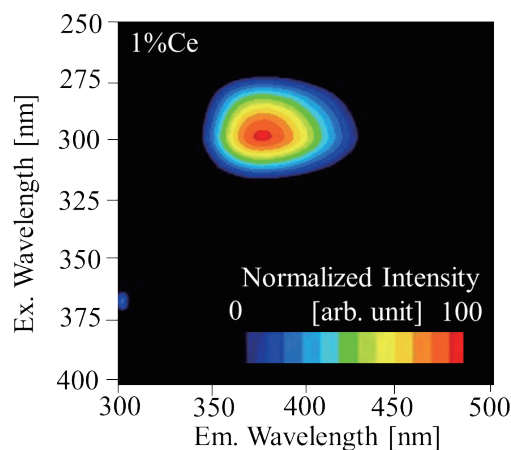


Fig. 4. (Color online) PL excitation and emission map of 1% Ce-doped BaHfO<sub>3</sub> sample.

the as-synthesized samples showed a rather low luminescence intensity. The horizontal and vertical axes are emission and excitation wavelengths, respectively. All the samples exhibited the broad luminescence band at  $\sim 370$  nm under the excitation wavelength of  $\sim 300$  nm. These emission and excitation wavelengths were similar to those in previously reported results of Ce-doped BaHfO<sub>3</sub>.<sup>(41,51)</sup> The PL *QY*s were 11.6% for the 0.3% sample, 30.5% for the 1% sample, 18.0% for the 3% sample, and 11.8% for the 5% sample. The highest PL *QY* was observed in the 1% sample, which was colorless compared with the same sample before treatment. The brownish color is attributed to Ce<sup>4+</sup>.<sup>(52)</sup> The sample treatment was conducted to suppress the formation of Ce<sup>4+</sup> ions because Ce<sup>4+</sup> ions do not contribute to the luminescence. Thus, the colorless or white sample involved less Ce<sup>4+</sup> ions and emitted luminescence due to the 5d–4f transition of Ce<sup>3+</sup>, leading to an increase in the PL *QY*.

Figure 5 shows the PL decay curves of Ce-doped BaHfO<sub>3</sub>. The excitation and monitoring wavelengths were 280 and 370 nm, respectively. The decay curves were fitted by one exponential function. The obtained PL decay time is listed in Table 1. The PL decay time of  $\sim 17$  ns was faster

than the typical decay time due to the 5d–4f transition of  $\text{Ce}^{3+}$ . For example, the decay times were  $\sim 60$  ns (Ce-doped  $\text{Gd}_2\text{SiO}_5$ ),<sup>(53)</sup>  $\sim 40$  ns (Ce-doped  $\text{Lu}_2\text{SiO}_5$ ),<sup>(54)</sup> and  $\sim 100$  ns (Ce-doped  $\text{Y}_3\text{Al}_5\text{O}_{12}$ ).<sup>(55)</sup> In contrast, the decay time of Ce-doped  $\text{YAlO}_3$  and  $\text{LuAlO}_3$  was  $\sim 17$  ns.<sup>(4)</sup> Shorter wavelengths and higher refractive indices are associated with faster decay times. The emission wavelength of Ce-doped  $\text{BaHfO}_3$  was relatively short, and the refractive index was greater than 2.<sup>(56)</sup> Therefore, the decay time of Ce-doped  $\text{BaHfO}_3$  was fast.

Figure 6 shows the X-ray-induced scintillation spectra of Ce-doped  $\text{BaHfO}_3$ . The peak wavelength was  $\sim 380$  nm, which was slightly shifted to a longer wavelength compared with the PL emission peak. The measurement geometry of X-ray-induced scintillation spectra was of the transmission type. In contrast, the PL spectrum measurement was conducted in the reflection-type geometry. Thus, the scintillation light was absorbed by the sample, and the peak wavelength was shifted to a longer wavelength.

Figure 7 shows the X-ray-induced scintillation decay curves of Ce-doped  $\text{BaHfO}_3$ . The observed decay curves contained fast and slow decay components. The obtained decay time is

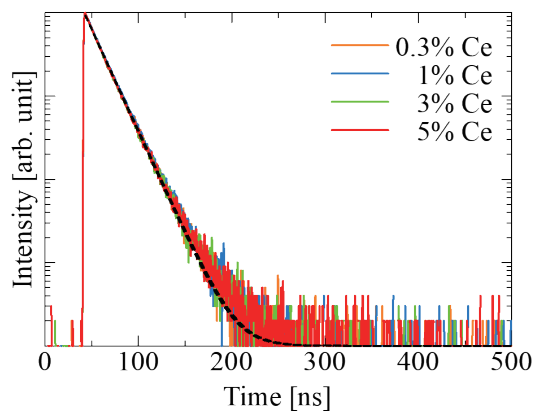


Fig. 5. (Color online) PL decay curves of Ce-doped  $\text{BaHfO}_3$  samples.

Table 1

PL and scintillation decay times of Ce-doped  $\text{BaHfO}_3$ .

Sample	PL decay time		Scintillation decay time	
	$\tau^1$ (ns)	$\tau^2$ (ns)	$\tau^1$ (ns)	$\tau^2$ (ns)
0.3% Ce	17	18 (96.3%)	375 (3.7%)	
1% Ce	17	16 (96.3%)	241 (3.7%)	
3% Ce	17	14 (98.4%)	352 (1.6%)	
5% Ce	17	15 (96.6%)	343 (3.4%)	

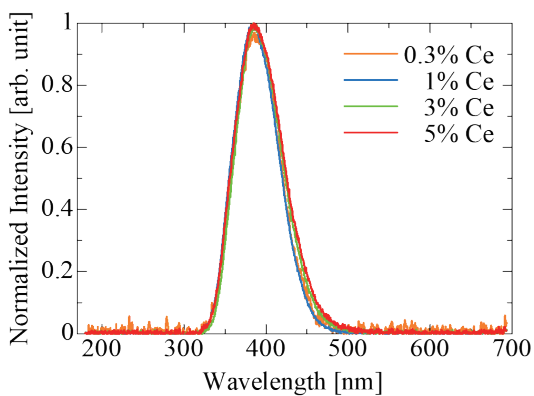


Fig. 6. (Color online) X-ray-induced scintillation spectra of Ce-doped  $\text{BaHfO}_3$  samples.

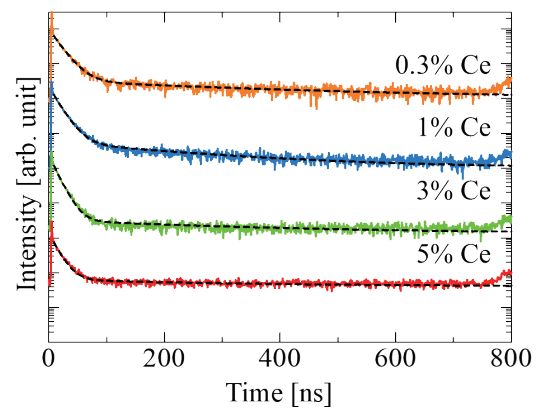


Fig. 7. (Color online) X-ray-induced scintillation decay curves of Ce-doped  $\text{BaHfO}_3$  samples.

listed in Table 1. The fast decay time was  $\sim 14\text{--}18$  ns, which was close to those in PL decay. The origin of the fast decay was attributed to the  $5d\text{--}4f$  transition of  $\text{Ce}^{3+}$  owing to the decay time, the broad emission band, and the emission wavelength, as shown in Fig. 5. The slow decay was typically observed in the Ce-doped  $\text{MHfO}_3$  ( $M = \text{Ca}$  and  $\text{Sr}$ ) series,<sup>(38,43,44,57)</sup> and the origin was attributed to some types of defect.

Figure 8 shows the afterglow curves of Ce-doped  $\text{BaHfO}_3$ . The afterglow level is defined as the ratio of the intensity at 20 ms after stopping X-ray exposure to the intensity during X-ray exposure. The afterglow levels of the 0.3, 1, 3, and 5% samples were 1550, 420, 1040, and 860 ppm, respectively. These afterglow levels were lower than those in the Ce-doped  $\text{MHfO}_3$  series.<sup>(38,43,45)</sup>

Figure 9 shows the pulse height distribution of the  $^{137}\text{Cs}$  gamma ray using Ce-doped  $\text{BaHfO}_3$  and  $\text{Bi}_4\text{Ge}_3\text{O}_{12}$  (BGO). The 1 and 3% samples exhibited a discriminable peak due to photoabsorption. The light yields of the 1 and 3% samples were 1600 and 1300 photons/MeV, respectively, compared with the peak position of BGO (6800 photons/MeV) and the quantum efficiency of PMT. Although the 3% sample had a black region on the sample surface, the peak was observed. Thus, the black region did not affect the results of the pulse height distribution. The reported integrated light yield of Ce-doped  $\text{BaHfO}_3$  was  $\sim 40000$  photons/MeV.<sup>(46)</sup> The integrated light yield is estimated on the basis of the integrated intensity of the scintillation spectrum compared with a reference and a sample. The integrated light yield depends on not only the light yield, but also the stopping power of materials.<sup>(58)</sup> Thus, we must evaluate the light yield using the pulse height distribution. The light yield of the present Ce-doped  $\text{BaHfO}_3$  was more than 10 times lower than the previous result.<sup>(46)</sup>

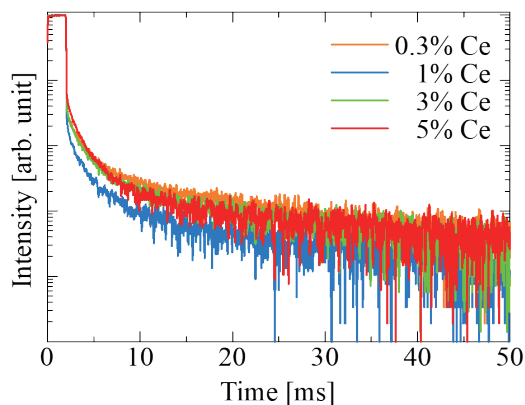


Fig. 8. (Color online) Afterglow curves of Ce-doped  $\text{BaHfO}_3$  samples.

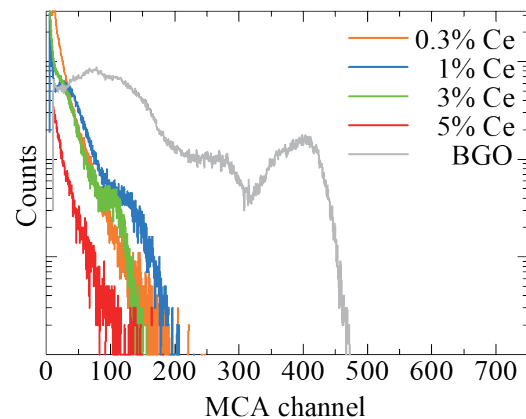


Fig. 9. (Color online) Pulse height distribution of  $^{137}\text{Cs}$  gamma ray using Ce-doped  $\text{BaHfO}_3$  samples.

## 4. Conclusions

The PL and scintillation properties of Ce-doped BaHfO<sub>3</sub> were investigated. The synthesized samples contained not only the BaHfO<sub>3</sub> phase but also the monoclinic HfO<sub>2</sub> phase. The as-synthesized BaHfO<sub>3</sub> showed low emission intensity. After the annealing treatment under the reduction condition, the emission intensity and the PL *QY* increased. The 1% sample exhibited the highest PL *QY* of 30.5% among the samples. The broad luminescence band at ~370–380 nm was observed in PL and scintillation. The PL and scintillation decay curves showed a fast decay of ~17 ns and a slow decay of ~241–375 ns. Ce-doped BaHfO<sub>3</sub> crystals exhibited a photoabsorption peak under <sup>137</sup>Cs gamma-ray irradiation, and the maximum light yield was 1600 photons/MeV. The Ce-doped MHfO<sub>3</sub> (*M* = Ca, Sr, and Ba) showed blue luminescence and fast decay under X-ray irradiation. The light yield of Ce-doped BaHfO<sub>3</sub> is lower than that of Ce-doped CaHfO<sub>3</sub>,<sup>(43)</sup> but higher than that of Ce-doped SrHfO<sub>3</sub>.<sup>(45)</sup>

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